

CMLDM7002A
 CMLDM7002AG*
 CMLDM7002AJ

**SURFACE MOUNT
 DUAL N-CHANNEL
 ENHANCEMENT-MODE
 SILICON MOSFET**

PICOmini™



SOT-563 CASE

* Device is *Halogen Free* by design

MAXIMUM RATINGS: ($T_A=25^\circ\text{C}$)

Drain-Source Voltage
 Drain-Gate Voltage
 Gate-Source Voltage
 Continuous Drain Current
 Continuous Source Current (Body Diode)
 Maximum Pulsed Drain Current
 Maximum Pulsed Source Current
 Power Dissipation (Note 1)
 Power Dissipation (Note 2)
 Power Dissipation (Note 3)
 Operating and Storage Junction Temperature
 Thermal Resistance



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DESCRIPTION:

These CENTRAL SEMICONDUCTOR devices are dual Enhancement-mode N-Channel Field Effect Transistors, manufactured by the N-Channel DMOS Process, designed for high speed pulsed amplifier and driver applications. The CMLDM7002A utilizes the USA pinout configuration, while the CMLDM7002AJ utilizes the Japanese pinout configuration. These devices offer low $r_{DS(ON)}$ and low $V_{DS(ON)}$.

MARKING CODES: CMLDM7002A: L02
 CMLDM7002AG*: C2G
 CMLDM7002AJ: 02J

SYMBOL		UNITS
V_{DS}	60	V
V_{DG}	60	V
V_{GS}	40	V
I_D	280	mA
I_S	280	mA
I_{DM}	1.5	A
I_{SM}	1.5	A
P_D	350	mW
P_D	300	mW
P_D	150	mW
T_J, T_{stg}	-65 to +150	$^\circ\text{C}$
θ_{JA}	357	$^\circ\text{C/W}$

ELECTRICAL CHARACTERISTICS PER TRANSISTOR: ($T_A=25^\circ\text{C}$ unless otherwise noted)

SYMBOL	TEST CONDITIONS	MIN	MAX	UNITS
I_{GSSF}, I_{GSSR}	$V_{GS}=20\text{V}, V_{DS}=0$		100	nA
I_{DSS}	$V_{DS}=60\text{V}, V_{GS}=0$		1.0	μA
I_{DSS}	$V_{DS}=60\text{V}, V_{GS}=0, T_J=125^\circ\text{C}$		500	μA
$I_{D(ON)}$	$V_{GS}=10\text{V}, V_{DS}=10\text{V}$	500		mA
BV_{DSS}	$V_{GS}=0, I_D=10\mu\text{A}$	60		V
$V_{GS(th)}$	$V_{DS}=V_{GS}, I_D=250\mu\text{A}$	1.0	2.5	V
$V_{DS(ON)}$	$V_{GS}=10\text{V}, I_D=500\text{mA}$		1.0	V
$V_{DS(ON)}$	$V_{GS}=5.0\text{V}, I_D=50\text{mA}$		0.15	V
V_{SD}	$V_{GS}=0, I_S=400\text{mA}$		1.2	V
$r_{DS(ON)}$	$V_{GS}=10\text{V}, I_D=500\text{mA}$		2.0	Ω
$r_{DS(ON)}$	$V_{GS}=10\text{V}, I_D=500\text{mA}, T_J=125^\circ\text{C}$		3.5	Ω
$r_{DS(ON)}$	$V_{GS}=5.0\text{V}, I_D=50\text{mA}$		3.0	Ω
$r_{DS(ON)}$	$V_{GS}=5.0\text{V}, I_D=50\text{mA}, T_J=125^\circ\text{C}$		5.0	Ω
gFS	$V_{DS}=10\text{V}, I_D=200\text{mA}$	80		mS

Notes: (1) Ceramic or aluminum core PC Board with copper mounting pad area of 4.0mm^2
 (2) FR-4 Epoxy PC Board with copper mounting pad area of 4.0mm^2
 (3) FR-4 Epoxy PC Board with copper mounting pad area of 1.4mm^2

R5 (18-January 2010)

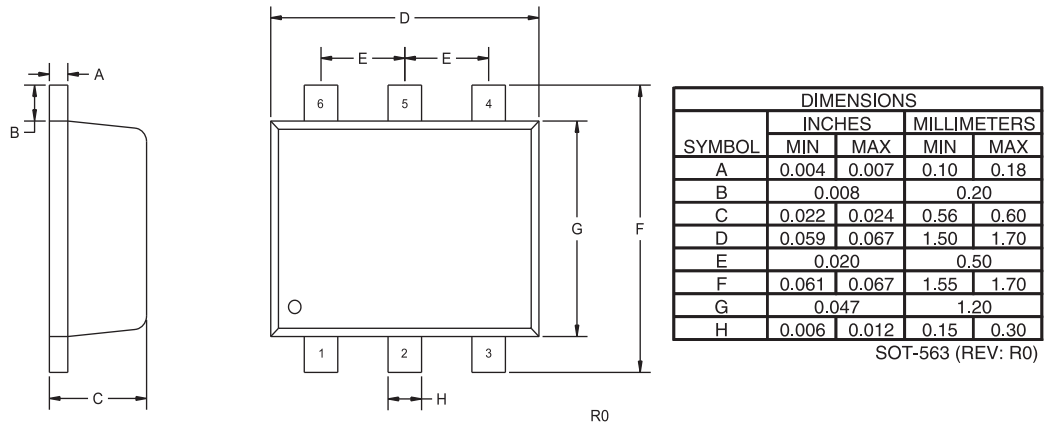
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ELECTRICAL CHARACTERISTICS PER TRANSISTOR - Continued: ($T_A=25^\circ\text{C}$ unless otherwise noted)

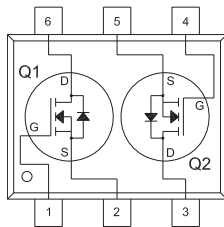
SYMBOL	TEST CONDITIONS	MIN	MAX	UNITS
C_{rss}	$V_{DS}=25\text{V}, V_{GS}=0, f=1.0\text{MHz}$		5.0	pF
C_{iss}	$V_{DS}=25\text{V}, V_{GS}=0, f=1.0\text{MHz}$		50	pF
C_{oss}	$V_{DS}=25\text{V}, V_{GS}=0, f=1.0\text{MHz}$		25	pF
t_{on} / t_{off}	$V_{DD}=30\text{V}, V_{GS}=10\text{V}, I_D=200\text{mA}$ $R_G=25\Omega, R_L=150\Omega$		20	ns

SOT-563 CASE - MECHANICAL OUTLINE



PIN CONFIGURATIONS

CMLDM7002A (USA Pinout)
CMLDM7002AG*

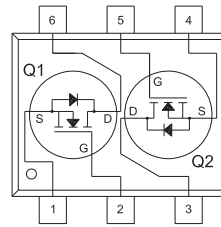


LEAD CODE:

- 1) Gate Q1
- 2) Source Q1
- 3) Drain Q2
- 4) Gate Q2
- 5) Source Q2
- 6) Drain Q1

MARKING CODES:
CMLDM7002A: L02
CMLDM7002AG*: C2G

CMLDM7002AJ (Japanese Pinout)



LEAD CODE:

- 1) Source Q1
- 2) Gate Q1
- 3) Drain Q2
- 4) Source Q2
- 5) Gate Q2
- 6) Drain Q1

MARKING CODE: 02J

* Device is **Halogen Free** by design

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